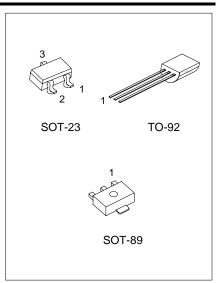
SENSITIVE GATE SILICON CONTROLLED RECTIFIERS REVERSE BLOCKING THYRISTORS

■ DESCRIPTION

PNPN devices designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits.

■ FEATURES

- * Sensitive gate allows triggering by micro controllers and other logic circuits
- * Blocking voltage to 600V
- * On-state current rating of 0.8A RMS at 80°C
- * High surge current capability 10A
- * Minimum and maximum values of I_{GT} , V_{GT} and I_{H} specified for ease of design
- * Immunity to dV/dt 20V/µsec minimum at 110
- * Glass-passivated surface for reliability and uniformity

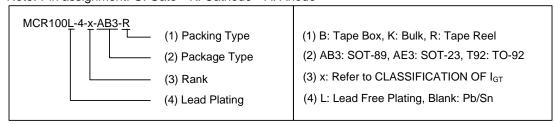


*Pb-free plating product number: MCR100L

■ ORDERING INFORMATION

Orderin	g Number	Dookogo	Pin assignment			Dooking
Normal	Lead Free Plating	Package	1	2	3	Packing
MCR100-4-x-AB3-R	MCR100L-4-x-AB3-R	SOT-89	G	Α	K	Tape Reel
MCR100-4-x-AE3-R	MCR100L-4-x-AE3-R	SOT-23	G	K	Α	Tape Reel
MCR100-4-x-T92-B	MCR100L-4-x-T92-B	TO-92	K	G	Α	Tape Box
MCR100-4-x-T92-K	MCR100L-4-x-T92-K	TO-92	K	G	Α	Bulk
MCR100-6-x-AB3-R	MCR100L-6-x-AB3-R	SOT-89	G	Α	K	Tape Reel
MCR100-6-x-AE3-R	MCR100L-6-x-AE3-R	SOT-23	G	K	Α	Tape Reel
MCR100-6-x-T92-B	MCR100L-6-x-T92-B	TO-92	K	G	Α	Tape Box
MCR100-6-x-T92-K	MCR100L-6-x-T92-K	TO-92	K	G	Α	Bulk
MCR100-8-x-AB3-R	MCR100L-8-x-AB3-R	SOT-89	G	Α	K	Tape Reel
MCR100-8-x-AE3-R	MCR100L-8-x-AE3-R	SOT-23	G	K	Α	Tape Reel
MCR100-8-x-T92-B	MCR100L-8-x-T92-B	TO-92	K	G	Α	Tape Box
MCR100-8-x-T92-K	MCR100L-8-x-T92-K	TO-92	K	G	Α	Bulk

Note: Pin assignment: G: Gate K: Cathode A: Anode



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■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT		
Peak Repetitive Off-State Voltage(Note)	MCR100-4		200	V	
(T _J =-40 ~ 110 , Sine Wave, 50 ~ 60Hz;	MCR100-6	V_{DRM}, V_{RRM}	400	V	
Gate Open)	MCR100-8		600	V	
On-Sate RMS Current		0.0	^		
(Tc=80) 180 Condition Angles		I _{T(RMS)}	0.8	A	
Peak Non-Repetitive Surge Current		I=	10	Α	
(1/2 cycle, Sine Wave, 60Hz, T _J =25)		I _{TSM}	10	A	
Circuit Fusing Considerations (t=8.3 ms)	l ² t	0.415	A ² s		
Forward Peak Gate Power (T _A =25 , Pulse)	P_GM	0.1	W		
Forward Average Gate Power (T _A =25 , t=8	$P_{G(AV)}$	0.1	W		
Peak Gate Current – Forward	I _{GM}	1	А		
(T _A =25 , Pulse Width≤1.0μs)		ı			
Peak Gate Voltage – Reverse	V.	5	V		
(T _A =25 , Pulse Width≤1.0μs)	V_{GRM}	5	V		
Operating Junction Temperature Range	T_J	-40 ~ + 110			
@ Rated V _{RRM} and V _{DRM}		-40 ~ +110			
Storage Temperature Range	T_{STG}	-40 ~ +150			

Note: V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	MAX	UNIT
The small Desigten as Austien to Ambient	0	200	/W
Thermal Resistance, Junction to Ambient SOT-23/SOT-89	$\theta_{\sf JA}$	400	/W

■ ELECTRICAL CHARACTERISTICS (T_J=25 , unless otherwise stated)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS		•			•		
Peak Forward or Reverse	T _C =25		V_D =Rated V_{DRM} and V_{RRM} ;			10	μА
Blocking Current	T _C =125	IDRM, IRRM	V_D =Rated V_{DRM} and V_{RRM} ; R_{GK} =1k Ω			100	μА
ON CHARACTERISTICS							
Peak Forward On-State Voltage (N	Note1)	V_{TM}	I _{TM} =1A Peak @ T _A =25			1.7	V
Gate Trigger Current (Continuous	DC)(Note2)	I _{GT}	V_{AK} =7Vdc, R_L =100 Ω , T_C =25		40	200	μА
Holding Current (Note 2)	T _C =25	Η	V _{AK} =7Vdc, initiating		0.5	5	mΑ
Holding Current (Note 3)	T _C =-40		current=20mA			10	mΑ
Latab Current	T _C =25		V 7V I 200 A		0.6	10	mΑ
Latch Current	T_{C} =-40	I _L	V _{AK} =7V, Ig=200μA			15	mΑ
Gate Trigger Voltage (continuous	T _C =25	\/	V 7Vda B 1000		0.62	0.8	V
dc) (Note 2)	T _C =-40	V_{GT}	V_{AK} =7Vdc, R_L =100 Ω			1.2	V
DYNAMIC CHARACTERISTICS							
			V _D =Rated V _{DRM} , Exponential				
Critical Rate of Rise of Off-State Voltage		d _∨ /dt	Waveform, $R_{GK}=1000\Omega$,	20	35		V/μs
			T _J =110			<u> </u>	
Critical Data of Diag of On State C	urront	al:/al#	I _{PK} =20A; Pw=10μsec;			50	Λ/
Critical Rate of Rise of On-State Current		di/dt	diG/dt=1A/μsec, Igt=20mA			50	A/μs

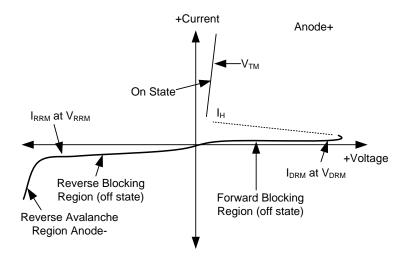
Note: 1. Indicates Pulse Test Width≤1.0ms, duty cycle ≤1%

- 2. R_{GK} =1000 Ω included in measurement.
- 3. Does not include R_{GK} in measurement.



■ VOLTAGE CURRENT CHARACTERISTIC OF SCR

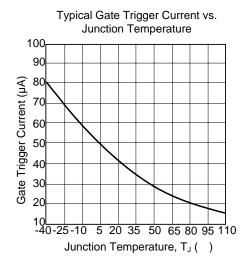
PARAMETER	SYMBOL
Peak Repetitive Off Stat Forward Voltage	V_{DRM}
Peak Forward Blocking Current	I _{DRM}
Peak Repetitive Off State Reverse Voltage	V_{RRM}
Peak Reverse Blocking Current	I _{RRM}
Peak On State Voltage	V_{TM}
Holding Current	I _H

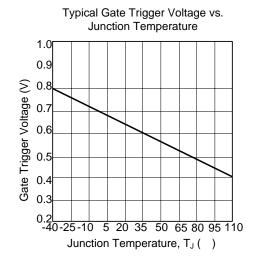


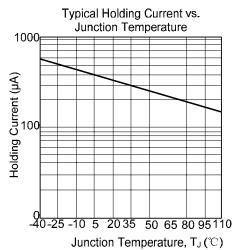
■ CLASSIFICATION OF I_{GT}

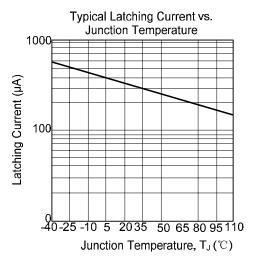
RANK	В	С	AA	AB	AC	AD
RANGE	48~105μA	95~200μΑ	8~16μΑ	14~21μA	19~25μΑ	23~52μΑ

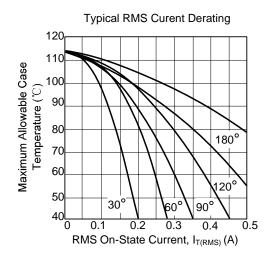
■ TYPICAL CHARACTERISTICS

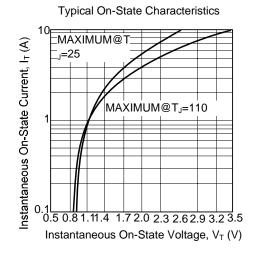












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